

# BCW65ALT1G, BCW65CLT1G

## General Purpose Transistor

### NPN Silicon

#### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	32	Vdc
Collector – Base Voltage	$V_{CBO}$	60	Vdc
Emitter – Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	$I_C$	800	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

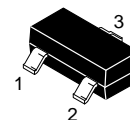
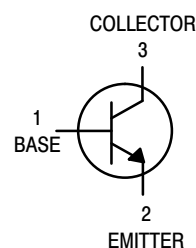
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.



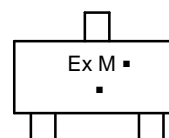
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SOT-23  
CASE 318  
STYLE 6

#### MARKING DIAGRAMS



Ex = Device Code  
x = A or C  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
BCW65ALT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BCW65CLT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BCW65ALT1G, BCW65CLT1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	32	–	–	V <sub>dc</sub>
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 μA <sub>dc</sub> , V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	60	–	–	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	–	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 32 V <sub>dc</sub> , I <sub>E</sub> = 0) (V <sub>CE</sub> = 32 V <sub>dc</sub> , I <sub>E</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>CES</sub>	–	–	20	nA <sub>dc</sub> μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 V <sub>dc</sub> , I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	–	20	nA <sub>dc</sub>

### ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = 100 μA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 2.0 V <sub>dc</sub> )	BCW65ALT1	h <sub>FE</sub>	35 75 100 35	– – – –	– – 250 –	–
DC Current Gain (I <sub>C</sub> = 100 μA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 2.0 V <sub>dc</sub> )	BCW65CLT1	h <sub>FE</sub>	80 180 250 100	– – – –	– – 630 –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , I <sub>B</sub> = 10 mA <sub>dc</sub> )		V <sub>CE(sat)</sub>	– –	0.7 0.3	– –	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> )		V <sub>BE(sat)</sub>	–	–	2.0	V <sub>dc</sub>

### SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I <sub>C</sub> = 20 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	100	–	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	–	12	pF
Input Capacitance (V <sub>EB</sub> = 0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	–	80	pF
Noise Figure (V <sub>CE</sub> = 5.0 V <sub>dc</sub> , I <sub>C</sub> = 0.2 mA <sub>dc</sub> , R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

### SWITCHING CHARACTERISTICS

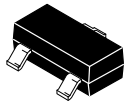
Turn–On Time (I <sub>B1</sub> = I <sub>B2</sub> = 15 mA <sub>dc</sub> )	t <sub>on</sub>	–	–	100	ns
Turn–Off Time (I <sub>C</sub> = 150 mA <sub>dc</sub> , R <sub>L</sub> = 150 Ω)	t <sub>off</sub>	–	–	400	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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### SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

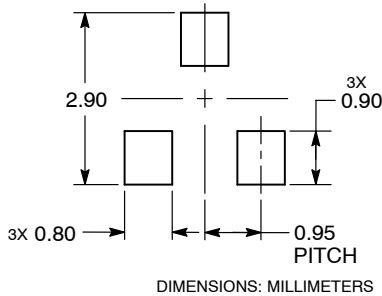


NOTES:

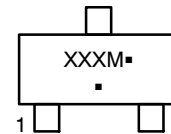
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

### RECOMMENDED SOLDERING FOOTPRINT



### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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